Am9122/Am91L22

256x4 Static RAM

DISTINCTIVE CHARACTERISTICS

- High-performance replacement for 93422/93L422
- Fast access times — as low as 25 ns
- Low-power dissipation
  - Low power: 440 mW (Commercial)
    495 mW (Military)
- Single 5-volt power supply — ±10% tolerance both Commercial and Military

GENERAL DESCRIPTION

The Am9122/Am91L22 Series is a MOS pin-for-pin and functional replacement for the 93422/93L422 bipolar memories. These devices are high-performance, low-power, 1024-bit, static, read/write random access memories. They offer a wide range of access times including versions as fast as 25 ns. Each memory is implemented as 256 words by 4 bits per word. This organization permits efficient

design of small memory systems and allows finer resolution of incremental memory depth.

The Am9122/91L22 employs an output enable and two chip enable inputs to give the user better data control. High noise immunity, high output drive (4 TTL loads) and TTL logic voltage levels allow easy conversion from bipolar to MOS. 10% power supply tolerances give better margins in the memory system.

BLOCK DIAGRAM

BD000060
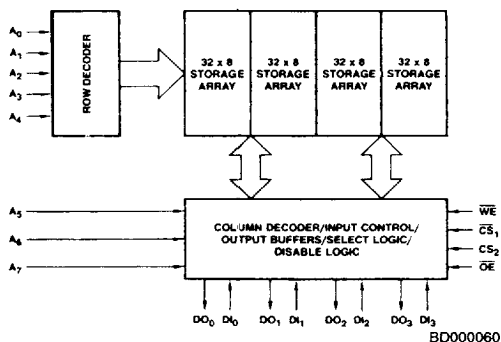
MODE SELECT TABLE

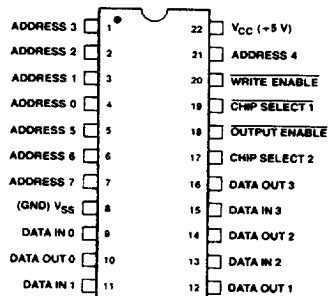| Inputs						
$\overline{OE}$	$\overline{CS}_1$	CS_2	$\overline{WE}$	D_0-D_3	Outputs	Mode
X	H	X	X	X	Hi-Z	Not Selected
X	X	L	X	X	Hi-Z	Not Selected
L	L	H	H	X	O_0-O_3	Read Stored Data
X	L	H	L	L	Hi-Z	Write "0"
X	L	H	L	H	Hi-Z	Write "1"
H	L	H	H	X	Hi-Z	Output Disabled
H	L	H	L	L	Hi-Z	Write "0" (Output Disabled)
H	L	H	L	H	Hi-Z	Write "1" (Output Disabled)

H = HIGH Voltage
L = LOW Voltage
X = Don't Care (HIGH or LOW)
Hi-Z = High Impedance

PRODUCT SELECTOR GUIDE

Part Number		Am9122-25	Am9122-35	Am91L22-35	Am91L22-45
Maximum Access Time (ns)		25	35	35	45
Maximum Operating Current (mA)	0° to +70°C	120	120	80	80
	−55° to +125°C	N/A	135	N/A	90

CONNECTION DIAGRAM
Top View

DIPs

ADDRESS 3	1	22	V_{CC} (+5 V)
ADDRESS 2	2	21	ADDRESS 4
ADDRESS 1	3	20	WRITE ENABLE
ADDRESS 0	4	19	CHIP SELECT 1
ADDRESS 5	5	18	OUTPUT ENABLE
ADDRESS 6	6	17	CHIP SELECT 2
ADDRESS 7	7	16	DATA OUT 3
(GND) V_{SS}	8	15	DATA IN 3
DATA IN 0	9	14	DATA OUT 2
DATA OUT 0	10	13	DATA IN 2
DATA IN 1	11	12	DATA OUT 1

CD000111

Note: Pin 1 is marked for orientation.

METALLIZATION AND PAD LAYOUT

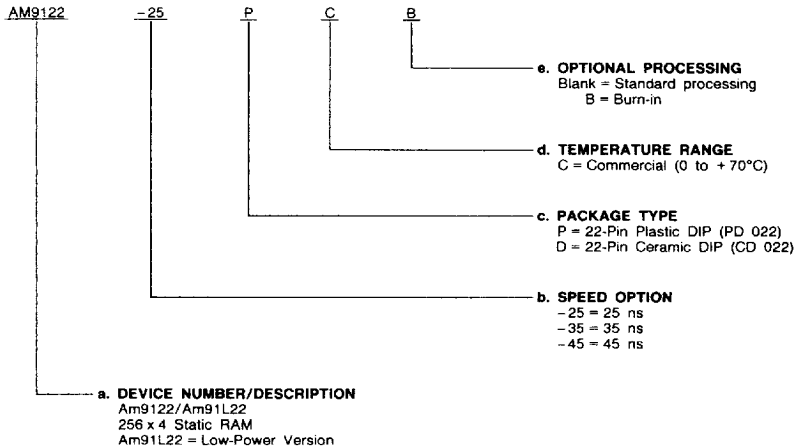| Address Designators	
External	Internal
A_0	A_0
A_1	A_1
A_2	A_2
A_3	A_3
A_4	A_4
A_5	A_5
A_6	A_6
A_7	A_7
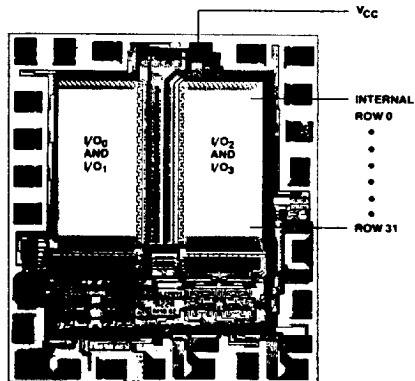
ORDERING INFORMATION

Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of:
a. **Device Number**
b. **Speed Option** (if applicable)
c. **Package Type**
d. **Temperature Range**
e. **Optional Processing**

```
AM9122    -25    P    C    B
```

e. OPTIONAL PROCESSING
Blank = Standard processing
B = Burn-in

d. TEMPERATURE RANGE
C = Commercial (0 to +70°C)

c. PACKAGE TYPE
P = 22-Pin Plastic DIP (PD 022)
D = 22-Pin Ceramic DIP (CD 022)

b. SPEED OPTION
-25 = 25 ns
-35 = 35 ns
-45 = 45 ns

a. DEVICE NUMBER/DESCRIPTION
Am9122/Am91L22
256 x 4 Static RAM
Am91L22 = Low-Power Version

Valid Combinations	
AM9122-25	
AM91L22-35	DC, DCB,
AM9122-35	PC, PCB
AM91L22-45	

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult MSIS sales department to confirm availability of specific valid combinations, and to obtain additional data on MSIS's standard military grade products.
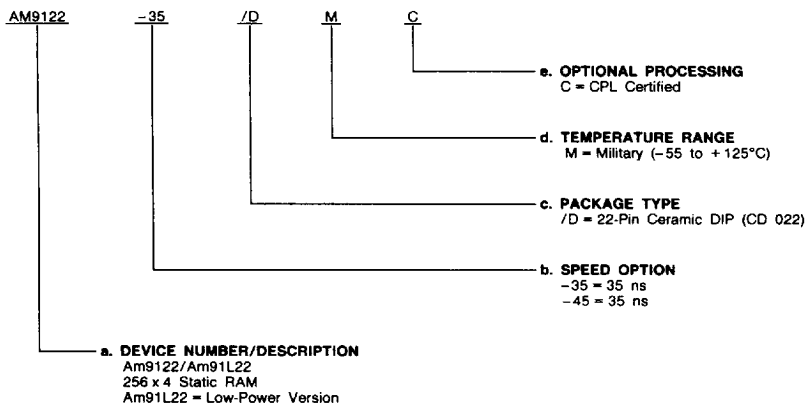
MILITARY ORDERING INFORMATION

CPL Products

AMD products for Aerospace and Defense applications are available in several packages and operating ranges. CPL (Controlled Products List) products are processed in accordance with MIL-STD-883C, but are inherently non-compliant because of packages, solderability, or surface treatment exceptions to those specifications. The order number (Valid Combination) is formed by a combination of: **a. Device Number**

b. Speed Option (if applicable)
c. Package Type
d. Temperature Range
e. Optional Processing

```
AM9122        -35      /D      M      C
```

e. OPTIONAL PROCESSING
   C = CPL Certified

d. TEMPERATURE RANGE
   M = Military (-55 to +125°C)

c. PACKAGE TYPE
   /D = 22-Pin Ceramic DIP (CD 022)

b. SPEED OPTION
   -35 = 35 ns
   -45 = 35 ns

a. DEVICE NUMBER/DESCRIPTION
   Am9122/Am91L22
   256 x 4 Static RAM
   Am91L22 = Low-Power Version

Valid Combinations	
AM9122-35	/DMC
AM91L22-45	

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult MSIS sales department to confirm availability of specific valid combinations, and to obtain additional data on MSIS's standard military grade products.

Group A Tests

Group A tests consist of Subgroups
1, 2, 3, 7, 8, 9, 10, 11.

PIN DESCRIPTION

$A_0 - A_7$ Address (Input)
The 8 address inputs select one of the 256 4-bit words in the RAM.

$\overline{CS}_1$ Chip Select 1 (Input)

CS_2 Chip Select 2 (Input)
$\overline{CS}_1$ is active LOW and CS_2 is active HIGH. The device can be accessed only when both Chip Selects are active. If either Chip Select is not active, the device is deselected and the outputs will be in a high-impedance state.

$\overline{WE}$ Write Enable Input
$\overline{WE}$ controls read and write operations. When $\overline{WE}$ is HIGH and $\overline{OE}$ is LOW, data will be present at the data outputs. When $\overline{WE}$ is LOW, data present on the data inputs will be written into the selected memory location. The data outputs will be in a high-impedance state.

$\overline{OE}$ Output Enable (Input)
$\overline{OE}$ controls the state of the data outputs in conjunction with Chip Select and $\overline{WE}$.

$DI_0 - DI_3$ Data IN (Input)
Data inputs to the RAM.

$DO_0 - DO_3$ Data Out (Output)
Data output from the RAM. The data output will be in a high-impedance state when either Chip Select is not active or $\overline{OE}$ is HIGH or $\overline{WE}$ is LOW.

V_{CC} Power Supply +5 Volts

V_{SS} Ground

8077984 0000006 60T

ABSOLUTE MAXIMUM RATINGS (Note 1)

Storage Temperature .... −65 to +150°C
Ambient Temperature with
  Power Applied .... −55 to +125°C
Supply Voltage .... −0.5 V to +7.0 V
DC Voltage Applied to Outputs .... −0.5 V to +7.0 V
DC Input Voltage .... −0.5 V to +7.0 V
Power Dissipation .... 1.0 W
DC Output Current .... 20 mA

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES (Note 2)

Commercial (C) Devices
  Ambient Temperature (T_A) .... 0 to +70°C
  Supply Voltage (V_{CC}) .... +4.5 V to +5.5 V

Military (M) Devices
  Ambient Temperature (T_A) .... −55 to +125°C
  Supply Voltage (V_{CC}) .... +4.5 V to +5.5 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating ranges unless otherwise specified (for CPL Products, Group A, Subgroups 1, 2, 3 are tested unless otherwise noted)

Parameter Symbol	Parameter Description	Test Conditions		Am91L22-35 Am91L22-45			Am9122-25 Am9122-35			Unit
				Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min.	I_{OH} = −5.2 mA	2.4			2.4			V
V_{OL}	Output LOW Voltage	V_{CC} = Min.	I_{OL} = 8.0 mA			0.4			0.4	V
V_{IH}	Input HIGH Voltage			2.1		V_{CC}	2.1		V_{CC}	V
V_{IL}	Input LOW Voltage			−2.5		0.8	−2.5		0.8	V
I_{IL}	Input LOW Current	V_{CC} = Max., V_{IN} = GND		−10			−10			µA
I_{IH}	Input HIGH Current	V_{CC} = Max., V_{IN} = V_{CC}				10			10	µA
V_{CD}	Input Diode Clamp Voltage					Note 3			Note 3	V
I_{OFF}	Output Current (Hi-Z)	$V_{OL} \leqslant V_{OUT} \leqslant V_{OH}$ Output Disabled	T_A = Max.	−10		10	−10		10	µA
I_{OS}	Output Short Circuit Current (Note 4)	V_{CC} = Max., V_{OUT} = GND	COM'L			−85			−85	mA
			MIL			−100			−100	
I_{CC}	Power Supply Current	V_{CC} = Max., I_{OUT} = 0 mA	T_A = 0°C			80			120	mA
			T_A = −55°C			90			135	
C_{IN}	Input Capacitance V_{IN} = 0 V	T_A = 25°C, f=1 MHz V_{CC} = 4.5 V (Note 5)			3	5		3	5	pF
C_{OUT}	Output Capacitance V_{OUT} = 0 V				5	8		5	8	

Notes: 1. Absolute Maximum Rating are intended for user guidelines and are not tested.
    2. For test and correlation purposes, ambient temperature is defined as the "instant-ON" case temperature.
    3. The NMOS process does not provide a clamp diode. However, the Am9122/91L22 is insensitive to −3 V DC input levels and −5 V undershoot pulses of less than 10 ns (measured at 50% point).
    4. For test purposes, not more than one output at a time should be shorted. Short circuit test duration should not exceed 30 seconds.
    5. These parameters are not 100% tested, but are evaluated at initial characterization and at any time the design is modified where capacitance may be affected.
    6. Test conditions assume signal transition times of 10 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance as in A under Switching Test Circuits.
    7. Transition is measured at 1.5 V on the input to V_{OH} − 500 mV and V_{OL} + 500 mV on the outputs using the load shown in B. C_L = 5 Pf.
    8. t_w measured at t_{wsa} = Min.; t_{wsa} measured at t_w = Min.

4

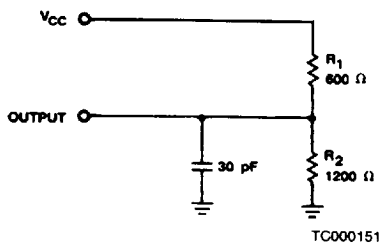## SWITCHING CHARACTERISTICS over operating ranges unless otherwise specified (for CPL Products, Group A, Subgroups 9, 10, 11 are tested unless otherwise noted) (Notes 6, 7, 8)
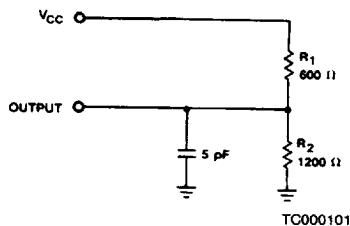
No.	Parameter Symbol	Parameter Description	Am9122-25 Min.	Am9122-25 Max.	Am91L22-35 Am9122-35 Min.	Am91L22-35 Am9122-35 Max.	Am91L22-45 Min.	Am91L22-45 Max.	Unit
1	t_{ACS}	Chip Select Time		15		25		30	ns
2	t_{ZRCS}	Chip Select to Hi-Z (Note 5 & 7)		20		30		30	ns
3	t_{AOS}	Output Enable Time		15		25		30	ns
4	t_{ZROS}	Output Enable to Hi-Z (Note 5 & 7)		20		30		30	ns
5	t_{AA}	Address Access Time		25		35		45	ns
6	t_{ZWS}	Write Disable to Hi-Z (Note 5 & 7)		20		30		35	ns
7	t_{WR}	Write Recovery Time		20		25		40	ns
8	t_W	Write Pulse Width (Note 8)	15		25		30		ns
9	t_{WSD}	Data Setup Time Prior to Write	5		5		5		ns
10	t_{WHD}	Data Hold Time After Write	5		5		5		ns
11	t_{WSA}	Address Setup Time (Note 8)	5		5		10		ns
12	t_{WHA}	Address Hold Time	5		5		5		ns
13	t_{WSCS}	Chip Select Setup Time	5		5		5		ns
14	t_{WHCS}	Chip Select Hold Time	5		5		5		ns

Notes: See notes following DC Characteristics table.

SWITCHING TEST CIRCUITS

V_{CC}

R_1 600 Ω

OUTPUT

30 pF

R_2 1200 Ω

TC000151

A

V_{CC}

R_1 600 Ω

OUTPUT

5 pF

R_2 1200 Ω

TC000101

B

SWITCHING TEST WAVEFORM

ALL INPUT PULSES

3.0 V p-p

90%

90%

GND

10%

10%

< 10 ns

< 10 ns

3.0 V p-p

90%

90%

GND

10%

10%

TW000021

Am9122/AM91L22

SWITCHING WAVEFORMS

KEY TO SWITCHING WAVEFORMS

KS000010

WF000660

Read Mode
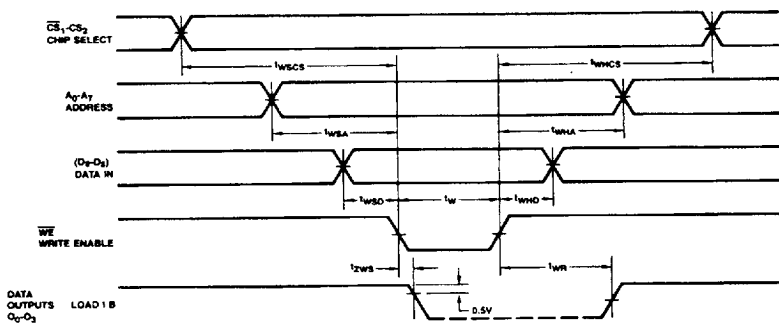
WF022050

Write Mode

(All above measurements implemented to 1.5 V unless otherwise stated.)

Note: Timing diagram represents one solution which results in an optimum cycle time. Timing may be changed in various applications as long as the worst-case limits are not violated.
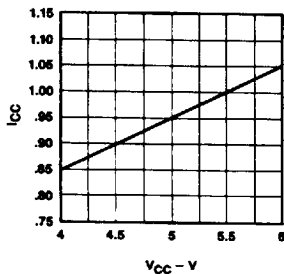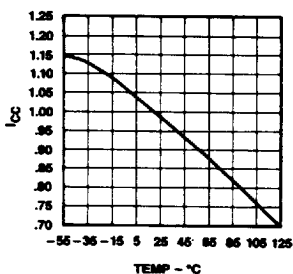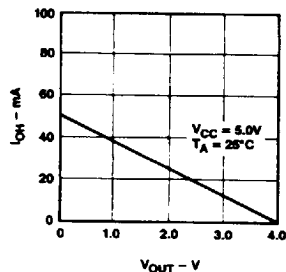
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TYPICAL PERFORMANCE CURVES

Normalized I_{CC} versus Supply Voltage
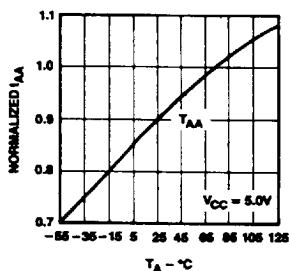

OP000120

Normalized I_{CC} versus Ambient Temperature

OP000130

Output Source Current versus Output Voltage

OP000140

Normalized Access Time versus Supply Voltage

OP000150
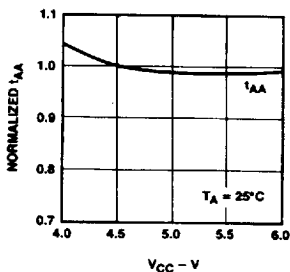
Normalized Access Time versus Ambient Temperature

OP000160

Output Sink Current versus Output Voltage

OP000170
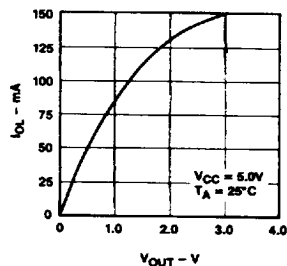
Access Time Change versus Input Voltage

OP000180
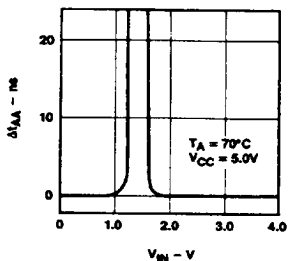
Access Time Change versus Output Loading

OP000190

Am9122/AM91L22

■ 8077984 0000010 030 ■